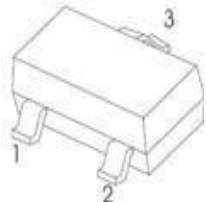
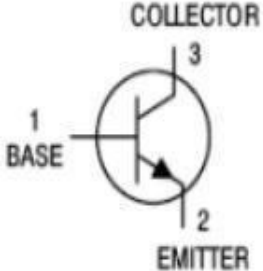


TRANSISTOR (PNP)	SOT-23 Plastic-Encapsulate Transistors
<p><u>SOT-23</u></p>   <p>1. BASE 2. EMITTER 3. COLLECTOR</p> <p>Marking :2L</p>	<p><b>Features</b></p> <ul style="list-style-type: none"> <li>※ Complimentary to MMBT5551</li> <li>※ Collector Current: <math>I_c=0.6A</math></li> <li>※ Ideal for Medium Power Amplification and Switching</li> </ul>

**MAXIMUM RATINGS (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	-160	V
Collector-Emitter Voltage	VCEO	-150	V
Emitter-Base Voltage	VEBO	-6	V
Collector Current	IC	-600	mA
Collector Power Dissipation	PC	450	mW
Thermal Resistance From Junction To Ambient	RθJA	625	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= -100μA, IE=0	-160	-255	-500	V
Collector-emitter breakdown voltage	V(BR)CEO	IC= -1mA, IB=0	-150	-251	-500	V
Emitter-base breakdown voltage	V(BR)EBO	IE= -10μA, IC=0	-6	-11	-30	V
Collector cut-off current	ICBO	VCB= -120 V , IE=0			-0.1	μ A
Collector cut-off current	ICEO	VCB= -150V , IE=0			-1.8	μ A
Emitter cut-off current	IEBO	VEB= -4V , IC=0			-0.1	μ A
DC current gain	hFE	VCE=-5V, IC= -1mA	80			
	hFE	VCE=-5V, IC= -10mA	100		200	
	hFE	VCE=-5V, IC= -50mA	50			
Collector-emitter saturation voltage	VCE(sat)	IC= -50 mA, IB= -5mA			-0.5	V
Base-emitter saturation voltage	VBE(sat)	IC= -50 mA, IB= -5mA			-1.	V
Transition frequency	fT	VCE=6V, IC= 20mA f=30MHz	100		300	MHz

### CLASSIFICATION OF hFE

<b>Rank</b>	<b>L</b>	<b>H</b>
<b>Range</b>	<b>100-200</b>	<b>200-300</b>
<b>MARKING</b>	<b>2L</b>	

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

